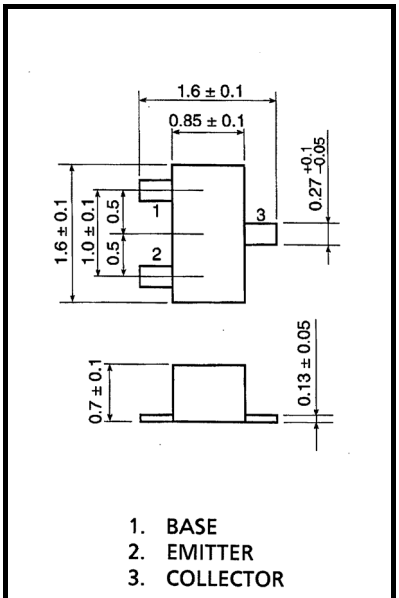
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2107F,RN2108F,RN2109F

Switching, Inverter Circuit, Interface Circuit
and Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1107F~RN1109F

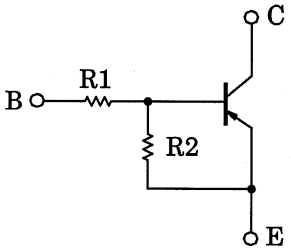
Unit: mm



JEDEC	—
EIAJ	—
TOSHIBA	2-2HA1A

Weight: 2.3 mg (typ.)

Equivalent Circuit and Bias Resister Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2107F	10	47
RN2108F	22	47
RN2109F	47	22

Absolute Maximum Ratings (Ta = 25°C)

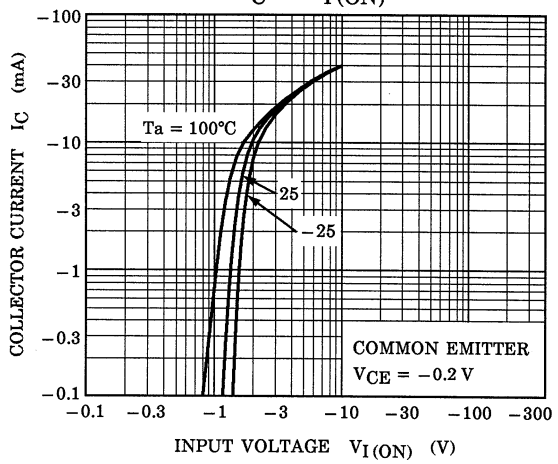
Characteristic		Symbol	Rating	Unit
Collector-base voltage	RN2107F ~RN2109F	V_{CBO}	−50	V
Collector-emitter voltage		V_{CEO}	−50	V
Emitter-base voltage	RN2107F	V_{EBO}	−6	V
	RN2108F		−7	
	RN2109F		−15	
Collector current	RN2107F ~RN2109F	I_C	−100	mA
Collector power dissipation		P_C	100	mW
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

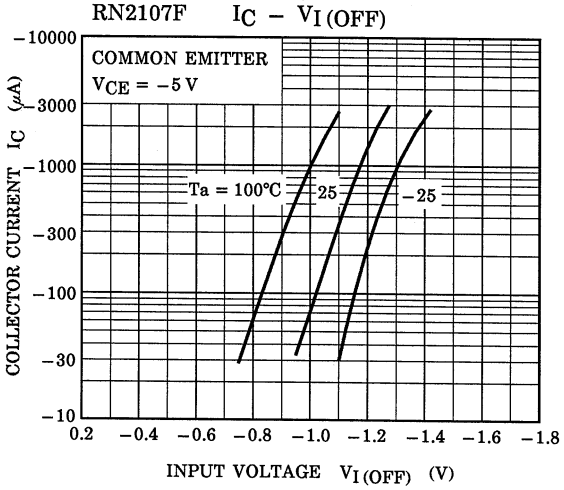
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2107F ~RN2109F	I_{CBO}	—	V_{CB} = −50V, I_E = 0	—	—	−100	nA
		I_{CEO}		V_{CE} = −50V, I_B = 0	—	—	−500	nA
Emitter cut-off current	RN2107F	I_{EBO}	—	V_{EB} = −6V, I_C = 0	−0.081	—	−0.15	mA
	RN2108F			V_{EB} = −7V, I_C = 0	−0.078	—	−0.145	
	RN2109F			V_{EB} = −15V, I_C = 0	−0.167	—	−0.311	
DC current gain	RN2107F	h_{FE}	—	V_{CE} = −5V, I_C = −10mA	80	—	—	—
	RN2108F				80	—	—	
	RN2109F				70	—	—	
Collector-emitter saturation voltage	RN2107F ~RN2109F	$V_{CE\ (sat)}$	—	I_C = −5mA, I_B = −0.25mA	—	−0.1	−0.3	V
Input voltage (ON)	RN2107F	$V_{I\ (ON)}$	—	V_{CE} = −0.2V, I_C = −5mA	−0.7	—	−1.8	V
	RN2108F				−1.0	—	−2.6	
	RN2109F				−2.2	—	−5.8	
Input voltage (OFF)	RN2107F	$V_{I\ (OFF)}$	—	V_{CE} = −5V, I_C = −0.1mA	−0.5	—	−1.0	V
	RN2108F				−0.6	—	−1.16	
	RN2109F				−1.5	—	−2.6	
Transition frequency	RN2107F ~RN2109F	f_T	—	V_{CE} = −10V, I_C = −5mA	—	200	—	MHz
Collector Output capacitance	RN2107F ~RN2109F	C_{ob}	—	V_{CB} = −10V, I_E = 0, f = 1MHz	—	3	6	pF
Input resistor	RN2107F	R1	—	—	7	10	13	kΩ
	RN2108F				15.4	22	28.6	
	RN2109F				32.9	47	61.1	
Resistor ratio	RN2107F	R1/R2	—	—	0.191	0.213	0.232	—
	RN2108F				0.421	0.468	0.515	
	RN2109F				1.92	2.14	2.35	

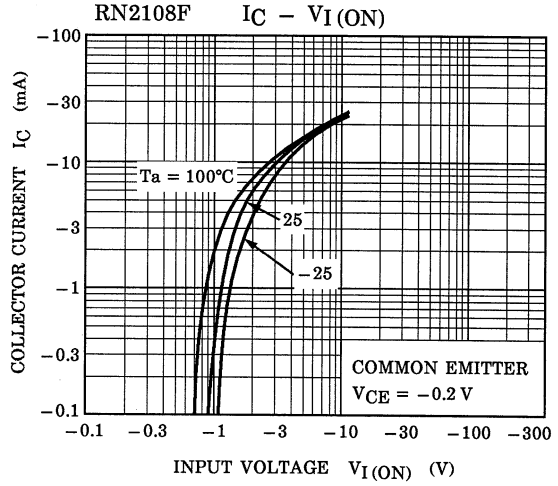
RN2107F $I_C - V_{I(ON)}$



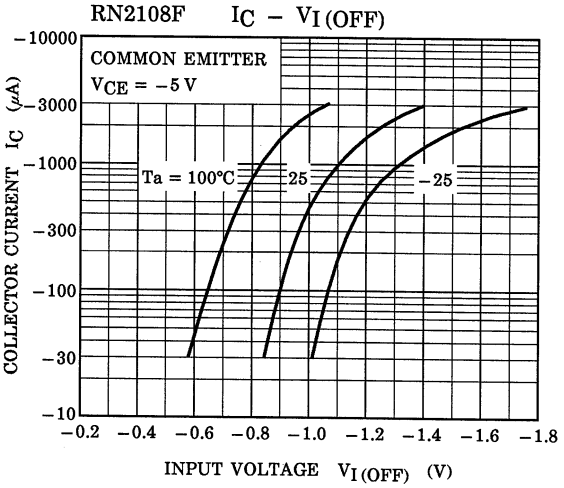
RN2107F $I_C - V_{I(OFF)}$



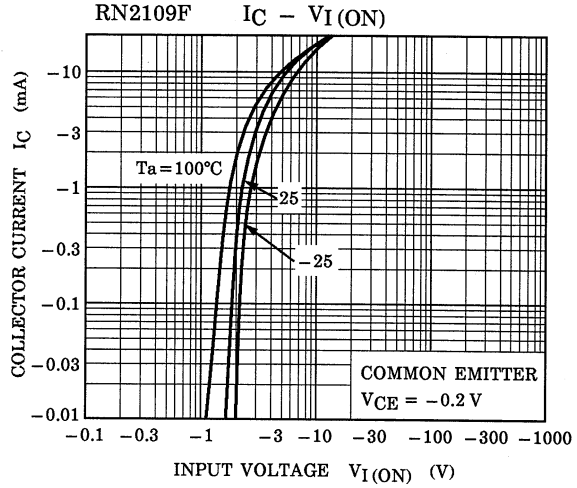
RN2108F $I_C - V_{I(ON)}$



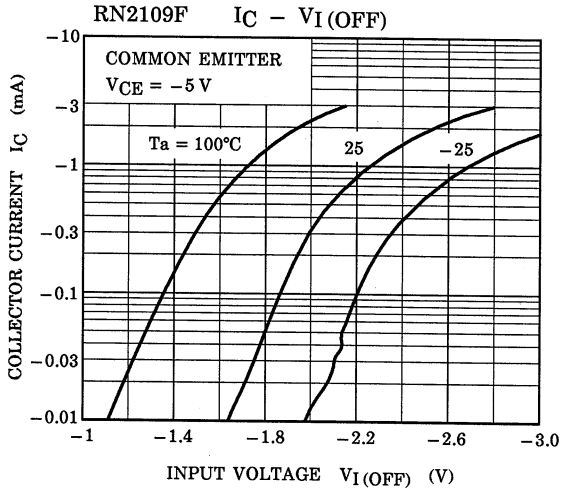
RN2108F $I_C - V_{I(OFF)}$



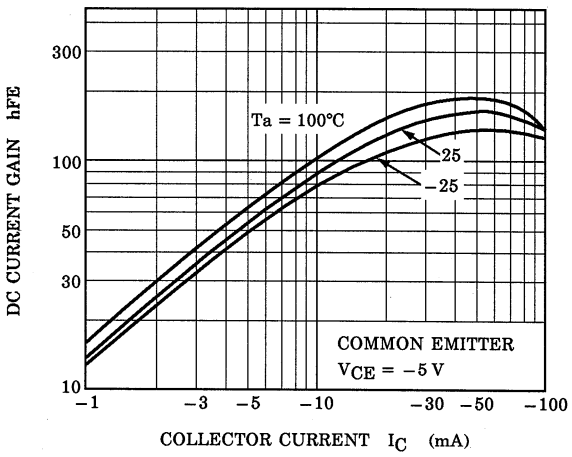
RN2109F $I_C - V_{I(ON)}$



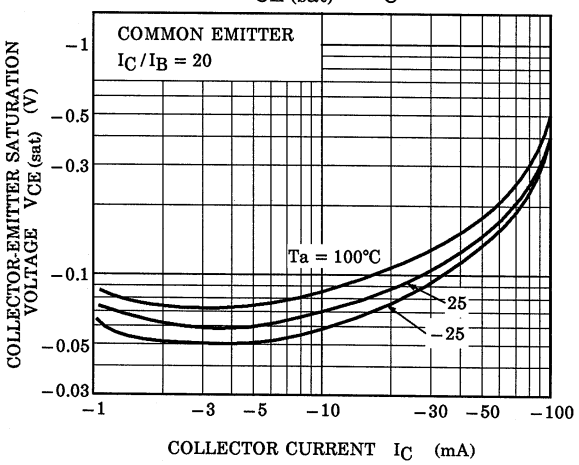
RN2109F $I_C - V_{I(OFF)}$



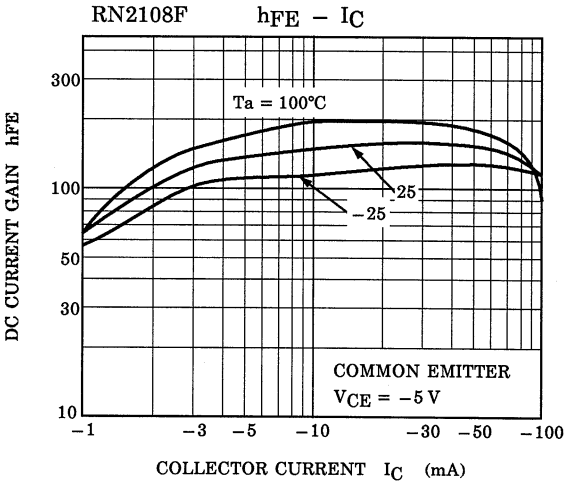
RN2107F h_{FE} – I_C



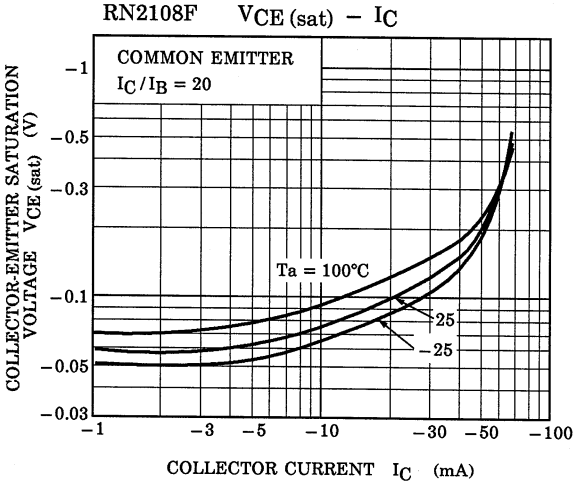
RN2107F $V_{CE\,(sat)}$ – I_C



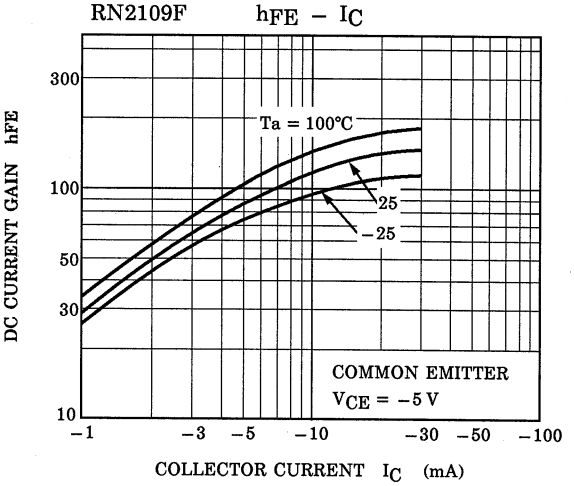
RN2108F h_{FE} – I_C



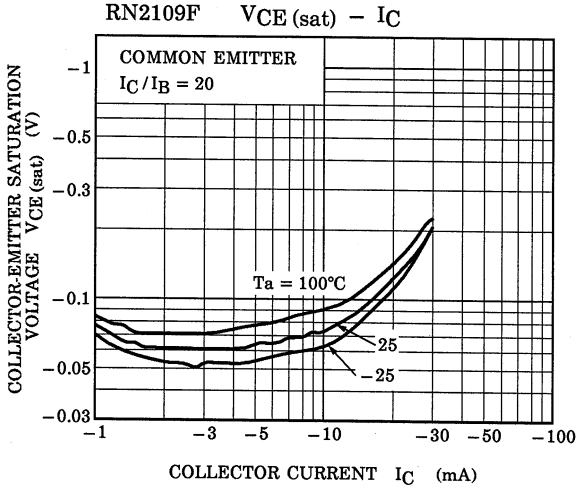
RN2108F $V_{CE\,(sat)}$ – I_C

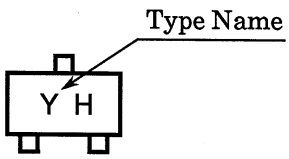
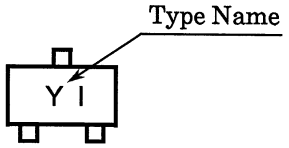


RN2109F h_{FE} – I_C



RN2109F $V_{CE\,(sat)}$ – I_C



Type Name	Marking
RN2107F	
RN2108F	
RN2109F	